

Tien-chang Lu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

308
papers

5,622
citations

37
h-index

59
g-index

413
ext. papers

6,341
ext. citations

3.2
avg, IF

5.41
L-index

#	Paper	IF	Citations
308	Development of surface plasmon polariton-based nanolasers. <i>Journal of Applied Physics</i> , 2022 , 131, 011104	10.4	1
307	Impact of Air-Hole on the Optical Performances of Epitaxially Regrown P-Side Up Photonic Crystal Surface-Emitting Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2022 , 28, 1-7	3.8	2
306	Pattern-tunable synthetic gauge fields in topological photonic graphene. <i>Nanophotonics</i> , 2022 , 11, 129761308	13.0	0
305	Improvement of output efficiency of p-face up photonic-crystal surface-emitting lasers. <i>Optics Express</i> , 2021 , 29, 11293-11300	3.3	1
304	Perovskite random lasers: a tunable coherent light source for emerging applications. <i>Nanotechnology</i> , 2021 , 32,	3.4	13
303	Study of an Epitaxial Regrowth Process by MOCVD for Photonic-Crystal Surface-Emitting Lasers. <i>Crystal Growth and Design</i> , 2021 , 21, 3521-3527	3.5	1
302	Hybrid Plasmonic Surface Lattice Resonance Perovskite Lasers on Silver Nanoparticle Arrays. <i>Advanced Optical Materials</i> , 2021 , 9, 2100299	8.1	6
301	Vertically integrated diffractive gratings on photonic crystal surface emitting lasers. <i>Scientific Reports</i> , 2021 , 11, 2427	4.9	1
300	Room-temperature active modulation of plasmonic nanolasers by current injection on hybrid graphene-insulator-metal platforms. <i>Journal of Applied Physics</i> , 2021 , 129, 053307	2.5	3
299	Low-Threshold Bound State in the Continuum Lasers in Hybrid Lattice Resonance Metasurfaces. <i>Laser and Photonics Reviews</i> , 2021 , 15, 2100118	8.3	13
298	Current Modulation of Plasmonic Nanolasers by Breaking Reciprocity on Hybrid Graphene-Insulator-Metal Platforms. <i>Advanced Science</i> , 2020 , 7, 2001823	13.6	8
297	Photonic integrated multiwavelength laser arrays: Recent progress and perspectives. <i>Applied Physics Letters</i> , 2020 , 116, 180501	3.4	5
296	Graphene-Loaded Plasmonic Zirconium Nitride and Gold Nanogroove Arrays for Surface-Charge Modifications. <i>ACS Applied Nano Materials</i> , 2020 , 3, 5002-5007	5.6	3
295	Electrically Injected GaN-Based Vertical-Cavity Surface-Emitting Lasers with TiO ₂ High-Index-Contrast Grating Reflectors. <i>ACS Photonics</i> , 2020 , 7, 861-866	6.3	13
294	Anti-guiding and guiding effects in GaN-based vertical-cavity surface-emitting lasers. <i>AIP Advances</i> , 2020 , 10, 025204	1.5	1
293	Observation of Femtosecond Acoustic Anomaly in a Solid Liquid Interface. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 2987-2993	3.8	2
292	Effect of Strains and V-Shaped Pit Structures on the Performance of GaN-Based Light-Emitting Diodes. <i>Crystals</i> , 2020 , 10, 311	2.3	4

291	Reproducible and Bendable SERS Substrates with Tailored Wettability Using Block Copolymers and Anodic Aluminum Oxide Templates. <i>Macromolecular Rapid Communications</i> , 2020 , 41, e2000088	4.8	2
290	Full-Spectrum Analysis of Perovskite-Based Surface Plasmon Nanolasers. <i>Nanoscale Research Letters</i> , 2020 , 15, 66	5	5
289	Effect of Passivation Layer on the Thin Film Perovskite Random Lasers. <i>Materials</i> , 2020 , 13,	3.5	1
288	Fabrication and Thermal Dissipation Properties of Carbon Nanofibers Derived from Electrospun Poly(Amic Acid) Carboxylate Salt Nanofibers. <i>Macromolecular Materials and Engineering</i> , 2020 , 305, 1900519	3.9	0
287	High Output Power GaN-Based Green Resonant-Cavity Light-Emitting Diodes With Trapezoidal Quantum Wells. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3650-3654	2.9	4
286	Perfect Absorption by an Atomically Thin Crystal. <i>Physical Review Applied</i> , 2020 , 14,	4.3	14
285	Improvement of Light Extraction in Deep Ultraviolet GaN Light Emitting Diodes with Mesh P-Contacts. <i>Applied Sciences (Switzerland)</i> , 2020 , 10, 5783	2.6	5
284	Structural Colors Enabled by Lattice Resonance on Silicon Nitride Metasurfaces. <i>ACS Nano</i> , 2020 , 14, 5678-5685	16.7	33
283	Demonstration of polarization control GaN-based micro-cavity lasers using a rigid high-contrast grating reflector. <i>Scientific Reports</i> , 2019 , 9, 13055	4.9	6
282	Photonic Crystal Surface Emitting Lasers with Naturally Formed Periodic ITO Structures. <i>ACS Photonics</i> , 2019 , 6, 684-690	6.3	8
281	Design and Fabrication of the Reliable GaN Based Vertical-Cavity Surface-Emitting Laser via Tunnel Junction. <i>Crystals</i> , 2019 , 9, 187	2.3	9
280	Flexible Organometal-Halide Perovskite Lasers for Speckle Reduction in Imaging Projection. <i>ACS Nano</i> , 2019 , 13, 5421-5429	16.7	54
279	Effects of three-dimensional strain distribution on the performance of GaN-based light-emitting diodes on patterned sapphire substrates. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SC1036	1.4	2
278	Plasmonic Nanolasers Enhanced by Hybrid Graphene-Insulator-Metal Structures. <i>Nano Letters</i> , 2019 , 19, 5017-5024	11.5	28
277	Degradation mechanisms of bias stress on nitride-based near-ultraviolet light-emitting diodes in salt water vapor ambient. <i>Microelectronic Engineering</i> , 2019 , 218, 111158	2.5	3
276	. <i>IEEE Journal of Quantum Electronics</i> , 2019 , 55, 1-4	2	6
275	Progress and prospects of GaN-based VCSEL from near UV to green emission. <i>Progress in Quantum Electronics</i> , 2018 , 57, 1-19	9.1	37
274	Ultracompact Pseudowedge Plasmonic Lasers and Laser Arrays. <i>Nano Letters</i> , 2018 , 18, 747-753	11.5	43

273	Characterization of spatial manipulation on ZnO nanocomposites consisting of Au nanoparticles, a graphene layer, and ZnO nanorods. <i>Applied Physics A: Materials Science and Processing</i> , 2018 , 124, 1	2.6	1
272	High-Performance Plasmonic Nanolasers with a Nanotrench Defect Cavity for Sensing Applications. <i>ACS Photonics</i> , 2018 , 5, 2638-2644	6.3	22
271	Design of photonic crystal surface emitting lasers with indium-tin-oxide top claddings. <i>Applied Physics Letters</i> , 2018 , 112, 061105	3.4	8
270	Fabrication and Thermal Insulation Properties of Bamboo-Shaped Polymer Fibers by Selective Solvent Vapor Annealing. <i>Macromolecular Rapid Communications</i> , 2018 , 39, e1800424	4.8	5
269	Photonic Crystal Surface Emitting Lasers with Novel Transparent Cladding Layers 2018 ,		1
268	Surface plasmon polariton nanolasers: Coherent light sources for new applications. <i>Chinese Physics B</i> , 2018 , 27, 114208	1.2	7
267	Three dimensional characterization of GaN-based light emitting diode grown on patterned sapphire substrate by confocal Raman and photoluminescence spectromicroscopy. <i>Scientific Reports</i> , 2017 , 7, 45519	4.9	11
266	Superior characteristics of microscale light emitting diodes through tightly lateral oxide-confined scheme. <i>Applied Physics Letters</i> , 2017 , 110, 021108	3.4	22
265	High-Efficiency InGaN/GaN CoreShell Nanorod Light-Emitting Diodes With Low-Peak Blueshift and Efficiency Droop. <i>IEEE Nanotechnology Magazine</i> , 2017 , 16, 355-358	2.6	12
264	Surface roughness effects on aluminium-based ultraviolet plasmonic nanolasers. <i>Scientific Reports</i> , 2017 , 7, 39813	4.9	20
263	Characteristics Improvement of Surface-Emitting Distributed Feedback Lasers With ITO Claddings. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2017 , 23, 1-6	3.8	3
262	High-temperature operation of GaN-based vertical-cavity surface-emitting lasers. <i>Applied Physics Express</i> , 2017 , 10, 112101	2.4	16
261	Electrically Pumped III-N Microcavity Light Emitters Incorporating an Oxide Confinement Aperture. <i>Nanoscale Research Letters</i> , 2017 , 12, 15	5	5
260	Collective Lasing Behavior of Monolithic GaN-InGaN Core-Shell Nanorod Lattice under Room Temperature. <i>Nano Letters</i> , 2017 , 17, 6228-6234	11.5	6
259	Exciton-polariton Josephson junctions at finite temperatures. <i>Scientific Reports</i> , 2017 , 7, 9515	4.9	7
258	Lasing on nonlinear localized waves in curved geometry. <i>Optics Express</i> , 2017 , 25, 29068	3.3	3
257	UVA light-emitting diode grown on Si substrate with enhanced electron and hole injections. <i>Optics Letters</i> , 2017 , 42, 4533-4536	3	23
256	Effects of Nanoscale V-Shaped Pits on GaN-Based Light Emitting Diodes. <i>Materials</i> , 2017 , 10,	3.5	6

255 GaN-Based Surface-Emitting Lasers. *Series in Optics and Optoelectronics*, **2017**, 557-594

254 Localized surface plasmon for enhanced lasing performance in solution-processed perovskites. *Optics Express*, **2016**, 24, 20696-702 3.3 22

253 Rapid separation of gold nanorods in multilayer aqueous systems via centrifugation. *RSC Advances*, **2016**, 6, 90786-90791 3.7 2

252 Single-crystalline aluminum film for ultraviolet plasmonic nanolasers. *Scientific Reports*, **2016**, 6, 19887 4.9 46

251 Significant improvement of GaN crystal quality with ex-situ sputtered AlN nucleation layers **2016**, 3

250 Effects of thickness on optical characteristics and strain distribution of thin-film GaN light-emitting diodes transferred to Si substrates. *Applied Physics Express*, **2016**, 9, 042101 2.4 5

249 ZnO-Based Microcavities Sculpted by Focus Ion Beam Milling. *Nanoscale Research Letters*, **2016**, 11, 319 5 5

248 Improved performance of GaN based light emitting diodes with ex-situ sputtered AlN nucleation layers. *AIP Advances*, **2016**, 6, 045311 1.5 17

247 3D numerical modeling of the carrier transport and radiative efficiency for InGaN/GaN light emitting diodes with V-shaped pits. *AIP Advances*, **2016**, 6, 055208 1.5 25

246 Crossover from polariton lasing to exciton lasing in a strongly coupled ZnO microcavity. *Scientific Reports*, **2016**, 6, 20581 4.9 15

245 Quantum-Dot Surface Emitting Distributed Feedback Lasers Using Indium Oxide as Top Claddings. *IEEE Photonics Technology Letters*, **2016**, 28, 1633-1636 2.2 9

244 Mode Switching of High Index Contrast Photonic Crystal Surface Emitting Lasers. *IEEE Journal of Quantum Electronics*, **2016**, 52, 1-5 2 9

243 High-Operation-Temperature Plasmonic Nanolasers on Single-Crystalline Aluminum. *Nano Letters*, **2016**, 16, 3179-86 11.5 83

242 Controllable lasing performance in solution-processed organic-inorganic hybrid perovskites. *Nanoscale*, **2016**, 8, 18483-18488 7.7 19

241 Light Emission Characteristics of Nonpolar GaInN -Plane GaN-Based Photonic Crystal Defect Cavities. *IEEE Journal of Quantum Electronics*, **2016**, 52, 1-7 2 2

240 Double superstructures in InGaN/GaN nano-pyramid arrays. *Superlattices and Microstructures*, **2015**, 86, 275-279 2.8 1

239 Fabrication of SiC membrane HCG blue reflector using nanoimprint lithography **2015**, 3

238 Ultrastrong Mode Confinement in ZnO Surface Plasmon Nanolasers. *ACS Nano*, **2015**, 9, 3978-83 16.7 76

237	Manipulation of nanoscale V-pits to optimize internal quantum efficiency of InGaN multiple quantum wells. <i>Applied Physics Letters</i> , 2015 , 106, 091104	3.4	39
236	Manipulation of exciton and photon lasing in a membrane-type ZnO microcavity. <i>Applied Physics Letters</i> , 2015 , 106, 131106	3.4	8
235	Lasing Characteristics of GaN-Based Photonic Quasi-Crystal Surface Emitting Lasers Operated at Higher Order Mode. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2015 , 21, 743-748	3.8	0
234	Effects of Lattice Types on GaN-Based Photonic Crystal Surface-Emitting Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2015 , 21, 426-431	3.8	1
233	Light Emitting Diodes. <i>Topics in Applied Physics</i> , 2015 , 179-234	0.5	
232	High density GaN/AlN quantum dots for deep UV LED with high quantum efficiency and temperature stability. <i>Scientific Reports</i> , 2014 , 4, 5166	4.9	31
231	High efficiency InGaN/GaN light emitting diodes with asymmetric triangular multiple quantum wells. <i>Applied Physics Letters</i> , 2014 , 104, 091111	3.4	16
230	Fabrication and characteristics of a GaN-based microcavity laser with shallow etched mesa. <i>Applied Physics Express</i> , 2014 , 7, 062101	2.4	5
229	Numerical analysis on current and optical confinement of III-nitride vertical-cavity surface-emitting lasers. <i>Optics Express</i> , 2014 , 22, 9789-97	3.3	14
228	Fabrication and characterization of back-side illuminated InGaN/GaN solar cells with periodic via-holes etching and Bragg mirror processes. <i>Optics Express</i> , 2014 , 22 Suppl 5, A1334-42	3.3	4
227	Lasing behaviors upon phase transition in solution-processed perovskite thin films. <i>Applied Physics Letters</i> , 2014 , 105, 231108	3.4	53
226	GaN-Based VCSELs. <i>Springer Series in Optical Sciences</i> , 2013 , 403-427	0.5	3
225	Study of Nonpolar GaN/ZnO Heterostructures Grown by Molecular Beam Epitaxy. <i>Crystal Growth and Design</i> , 2013 , 13, 3098-3102	3.5	7
224	Optical characterizations and reverse-bias electroluminescence observation for reliability investigations of the InGaN light emitting diode. <i>Microelectronic Engineering</i> , 2013 , 101, 42-46	2.5	11
223	Strong light-matter interaction in ZnO microcavities. <i>Light: Science and Applications</i> , 2013 , 2, e76-e76	16.7	99
222	Asymmetric design of photonic crystal surface-emitting lasers with low-threshold characteristics. <i>Applied Optics</i> , 2013 , 52, 5851-5	1.7	0
221	Growth and Characteristics of a-Plane GaN/ZnO/GaN Heterostructure. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1538, 303-307		
220	Depth-resolved confocal micro-Raman spectroscopy for characterizing GaN-based light emitting diode structures. <i>Review of Scientific Instruments</i> , 2013 , 84, 113108	1.7	10

219	High quality factor nonpolar GaN photonic crystal nanocavities. <i>Applied Physics Letters</i> , 2013 , 102, 1911164	5.4	8
218	830-nm AlGaAs-InGaAs Graded Index Double Barrier Separate Confinement Heterostructures Laser Diodes With Improved Temperature and Divergence Characteristics. <i>IEEE Journal of Quantum Electronics</i> , 2013 , 49, 127-132	2	8
217	GaN-based high contrast grating surface-emitting lasers. <i>Applied Physics Letters</i> , 2013 , 102, 081111	3.4	18
216	Localized Lasing Mode in GaN Quasi-Periodic Nanopillars at Room Temperature. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 4900206-4900206	3.8	11
215	Publisher's Note: Growth and Characteristics of a-Plane GaN on ZnO Heterostructure [J. Electrochem. Soc., 159, H290 (2012)]. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, X1-X1	2	5
214	The characteristics of the high- ϵ_r Er ₂ O ₃ (erbium oxide) dielectrics deposited on polycrystalline silicon. <i>Solid State Communications</i> , 2012 , 152, 504-508	1.6	28
213	Improved Output Power of InGaN-Based Ultraviolet LEDs Using a Heavily Si-Doped GaN Insertion Layer Technique. <i>IEEE Journal of Quantum Electronics</i> , 2012 , 48, 175-181	2	4
212	A novel randomly textured phosphor structure for highly efficient white light-emitting diodes. <i>Nanoscale Research Letters</i> , 2012 , 7, 188	5	30
211	. <i>IEEE Journal of Quantum Electronics</i> , 2012 , 48, 867-871	2	1
210	Erratum to "Design of low-threshold photonic crystal surface-emitting lasers" [May 15, 2012 866-868]. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 1358-1358	2.2	3
209	Light Extraction Enhancement of GaN-Based Light-Emitting Diodes Using Crown-Shaped Patterned Sapphire Substrates. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 1212-1214	2.2	6
208	Study of Band-Edge Modes in GaN-Based Photonic Crystal Surface-Emitting Lasers by the Multiple-Scattering Method. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2012 , 18, 1629-1635	3.8	9
207	Design of Low-Threshold Photonic Crystal Surface-Emitting Lasers. <i>IEEE Photonics Technology Letters</i> , 2012 ,	2.2	5
206	Ultraviolet emission efficiency enhancement of a-plane AlGaIn/GaN multiple-quantum-wells with increasing quantum well thickness. <i>Applied Physics Letters</i> , 2012 , 100, 261901	3.4	8
205	Enhanced internal quantum efficiency in graphene/InGaIn multiple-quantum-well hybrid structures. <i>Applied Physics Letters</i> , 2012 , 101, 061905	3.4	8
204	Characteristics of polarization emission in a-plane GaN-based multiple quantum wells structures. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1432, 79		
203	Efficiency and Droop Improvement in InGaIn/GaN Light-Emitting Diodes by Selective Carrier Distribution Manipulation. <i>Applied Physics Express</i> , 2012 , 5, 042101	2.4	3
202	High-Temperature Polariton Lasing in a Strongly Coupled ZnO Microcavity. <i>Applied Physics Express</i> , 2012 , 5, 082801	2.4	15

201	Light Output Enhancement of GaN-Based Light-Emitting Diodes by Optimizing SiO ₂ Nanorod-Array Depth Patterned Sapphire Substrate. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 04DG11	1.4	1
200	Room temperature polariton lasing vs. photon lasing in a ZnO-based hybrid microcavity. <i>Optics Express</i> , 2012 , 20, 5530-7	3.3	87
199	Sub-wavelength GaN-based membrane high contrast grating reflectors. <i>Optics Express</i> , 2012 , 20, 20551-3	3.3	27
198	The Differences in Optical Characteristics of TiO ₂ and TiO ₂ /AAO Nanotube Arrays Fabricated by Atomic Layer Deposition. <i>Journal of the Electrochemical Society</i> , 2012 , 159, K136-K140	3.9	14
197	Growth and Characteristics of a-Plane GaN on ZnO Heterostructure. <i>Journal of the Electrochemical Society</i> , 2012 , 159, H290-H292	3.9	8
196	High efficiency GaN-based light-emitting diodes with embedded air voids/SiO ₂ nanomasks. <i>Nanotechnology</i> , 2012 , 23, 045303	3.4	34
195	Recent advances on CW current injection blue VCSELs 2012 ,		5
194	Magnitude-tunable sub-THz shear phonons in a non-polar GaN multiple-quantum-well p-i-n diode. <i>Applied Physics Letters</i> , 2012 , 100, 201905	3.4	14
193	Light Output Enhancement of GaN-Based Light-Emitting Diodes by Optimizing SiO ₂ Nanorod-Array Depth Patterned Sapphire Substrate. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 04DG11	1.4	4
192	Room temperature current injection polariton light emitting diode with a hybrid microcavity. <i>Nano Letters</i> , 2011 , 11, 2791-5	11.5	29
191	Investigation of Emission Polarization and Strain in InGaN/GaN Multiple Quantum Wells on Nanorod Epitaxially Lateral Overgrowth Templates. <i>Journal of Lightwave Technology</i> , 2011 , 29, 2761-2765	4	3
190	. <i>Journal of Lightwave Technology</i> , 2011 , 29, 3757-3763	4	2
189	Characteristics of exciton-polaritons in ZnO-based hybrid microcavities. <i>Optics Express</i> , 2011 , 19, 4101-13	3.3	16
188	Threshold gain analysis in GaN-based photonic crystal surface emitting lasers. <i>Optics Letters</i> , 2011 , 36, 1908-10	3	12
187	Reduction of Efficiency Droop in Semipolar (110) InGaN/GaN Light Emitting Diodes Grown on Patterned Silicon Substrates. <i>Applied Physics Express</i> , 2011 , 4, 012105	2.4	32
186	Optical and Electrical Properties of GaN-Based Light Emitting Diodes Grown on Micro- and Nano-Scale Patterned Si Substrate. <i>IEEE Journal of Quantum Electronics</i> , 2011 , 47, 899-906	2	15
185	Optical Properties of A-Plane InGaN/GaN Multiple Quantum Wells Grown on Nanorod Lateral Overgrowth Templates. <i>IEEE Journal of Quantum Electronics</i> , 2011 , 47, 1101-1106	2	1
184	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 985-989	3.8	17

183	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 971-978	3.8	17
182	Characteristics of Current-Injected GaN-Based Vertical-Cavity Surface-Emitting Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 1594-1602	3.8	26
181	Broadening of upper polariton branch in GaAs, GaN, and ZnO semiconductor microcavities. <i>Applied Physics B: Lasers and Optics</i> , 2011 , 103, 137-144	1.9	5
180	Light Output Enhancement of UV Light-Emitting Diodes With Embedded Distributed Bragg Reflector. <i>IEEE Photonics Technology Letters</i> , 2011 , 23, 642-644	2.2	8
179	High Q microcavity light emitting diodes with buried AlN current apertures. <i>Applied Physics Letters</i> , 2011 , 99, 041101	3.4	16
178	Inverted Octagonal Surface Defects in a-Plane AlGaIn/GaN Multiple Quantum Wells. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H915	3.9	6
177	Efficiency and Droop Improvement in GaN-Based High-Voltage Light-Emitting Diodes. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1098-1100	4.4	42
176	Study of the internal quantum efficiency of InGaIn/GaN UV LEDs on patterned sapphire substrate using the electroluminescence method. <i>Journal of Crystal Growth</i> , 2011 , 315, 242-245	1.6	12
175	Optical properties of (1 10 1) semi-polar InGaIn/GaN multiple quantum wells grown on patterned silicon substrates. <i>Journal of Crystal Growth</i> , 2011 , 318, 500-504	1.6	15
174	Hole transport improvement in InGaIn/GaN light-emitting diodes by graded-composition multiple quantum barriers. <i>Applied Physics Letters</i> , 2011 , 99, 171106	3.4	114
173	GaN-based photonic crystal surface emitting lasers with central defects. <i>Applied Physics Letters</i> , 2011 , 99, 221105	3.4	6
172	GaN-Based LEDs Grown on HVPE Growth High Crystalline Quality Thick GaN Template. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H1103	3.9	7
171	Tunable Light Emission from GaN-Based Photonic Crystal with Ultraviolet AlN/AlGaIn Distributed Bragg Reflector. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 04DG09	1.4	3
170	Fabrication and Optical Properties of Green emission semipolar (101 1) InGaIn/GaN MQWs Selective Grown on GaN Nanopyramid Arrays. <i>Materials Research Society Symposia Proceedings</i> , 2011 , 1324, 37		
169	Exciton Localization Behaviors of Basal Stacking Faults in a-Plane AlGaIn Alloys. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H491	3.9	6
168	Improvement of quantum efficiency in green light-emitting diodes with pre-TMIn flow treatment. <i>Journal Physics D: Applied Physics</i> , 2011 , 44, 224015	3	3
167	Tunable Light Emission from GaN-Based Photonic Crystal with Ultraviolet AlN/AlGaIn Distributed Bragg Reflector. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 04DG09	1.4	
166	Reverse-Bias Electroluminescence Observation for Reliability Investigations of the InGaIn LED. <i>ECS Transactions</i> , 2010 , 27, 237-242	1	1

165	Low Droop Nonpolar GaN/InGaN Light Emitting Diode Grown on m-Plane GaN Substrate. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H501	3.9	19
164	Characteristics of efficiency droop in GaN-based light emitting diodes with an insertion layer between the multiple quantum wells and n-GaN layer. <i>Applied Physics Letters</i> , 2010 , 97, 251114	3.4	30
163	Efficiency droop alleviation in InGaN/GaN light-emitting diodes by graded-thickness multiple quantum wells. <i>Applied Physics Letters</i> , 2010 , 97, 181101	3.4	68
162	High efficiency InGaP/GaAs solar cell with Sub-wavelength structure on AlInP window layer 2010 ,		1
161	Characteristics of emission polarization in a-plane nanorods embedded with InGaN/GaN multiple quantum wells. <i>Journal of Applied Physics</i> , 2010 , 108, 063508	2.5	3
160	Highly-directional emission patterns based on near single guided mode extraction from GaN-based ultrathin microcavity light-emitting diodes with photonic crystals. <i>Applied Physics Letters</i> , 2010 , 97, 013108	3.4	25
159	Lasing characteristics at different band edges in GaN photonic crystal surface emitting lasers. <i>Applied Physics Letters</i> , 2010 , 96, 071108	3.4	14
158	Continuous wave operation of current injected GaN vertical cavity surface emitting lasers at room temperature. <i>Applied Physics Letters</i> , 2010 , 97, 071114	3.4	109
157	Low efficiency droop in blue-green m-plane InGaN/GaN light emitting diodes. <i>Applied Physics Letters</i> , 2010 , 96, 231101	3.4	136
156	Improvement in Crystalline Quality of InGaN-Based Epilayer on Sapphire via Nanoscaled Epitaxial Lateral Overgrowth. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 105501	1.4	5
155	Efficiency Improvement of Single-Junction In _{0.5} Ga _{0.5} P Solar Cell with Compositional Grading p-Emitter/Window Capping Configuration. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 122301	1.4	5
154	Hole injection and efficiency droop improvement in InGaN/GaN light-emitting diodes by band-engineered electron blocking layer. <i>Applied Physics Letters</i> , 2010 , 97, 261103	3.4	172
153	Self-Assembled Two-Dimensional Surface Structures for Beam Shaping of GaN-Based Vertical-Injection Light-Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 12-14	2.2	23
152	Study of InGaN/GaN Light-Emitting Diodes With Different Last Barrier Thicknesses. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 860-862	2.2	15
151	Stable Temperature Characteristics and Suppression of Efficiency Droop in InGaN Green Light-Emitting Diodes Using Pre-TMIn Flow Treatment. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 1279-1281	2.2	15
150	Abnormal polarization switching phenomenon in a-plane Al _x Ga _(1-x) N. <i>Optics Express</i> , 2010 , 18, 21743-9	3.3	3
149	Optical characteristics of a-plane ZnO/Zn _{0.8} Mg _{0.2} O multiple quantum wells grown by pulsed laser deposition. <i>Journal of Applied Physics</i> , 2010 , 108, 073504	2.5	25
148	Temperature-Dependent Electroluminescence Efficiency in Blue InGaN/GaN Light-Emitting Diodes With Different Well Widths. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 236-238	2.2	72

147	Investigation of wavelength-dependent efficiency droop in InGaN light-emitting diodes. <i>Applied Physics B: Lasers and Optics</i> , 2010 , 98, 779-789	1.9	42
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